

Complementary MOSFET

2NP08

■ Features

- N-Channel

$V_{DS} = 30V$, $I_D = 18A$

$R_{DS(ON)} = 15m\Omega$ @ $V_{GS}=10V$

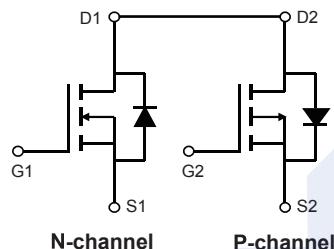
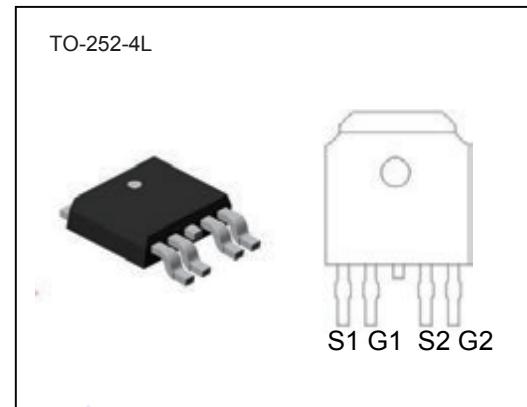
$R_{DS(ON)} = 20m\Omega$ @ $V_{GS}=4.5V$

- P-Channel

$V_{DS} = -30V$, $I_D = -14A$

$R_{DS(ON)} = 24m\Omega$ @ $V_{GS}=-10V$

$R_{DS(ON)} = 35m\Omega$ @ $V_{GS}=-4.5V$



■ Absolute Maximum Ratings ($T_A = 25^\circ C$ Unless otherwise specified)

Parameter	Symbol	N-CH	P-CH	Unit
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	
Continuous Drain Current	I_D (TA=25°C)	18	-14	A
	I_D (TA=70°C)	12	-9	
Pulsed Drain Current	I_{DM}	49	-35	
Power Dissipation	P_D (TA=25°C)	14		W
	P_D (TA=70°C)	7		
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	42		°C/W
Junction Temperature	T_J	150		°C
Storage Temperature Range	T_{stg}	-55 to 150		

Note 1. The device mounted on 1in² FR4 board with 2 oz copper

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■ Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless otherwise specified)

Parameter	Symbol	Test Conditions	Type	Min	Typ	Max	Unit
Static							
Drain-Source Breakdown Voltage	V_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	N-CH	30			V
		$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	P-CH	-30			
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$	N-CH			1	μA
		$V_{DS}=-30\text{V}, V_{GS}=0\text{V}$	P-CH			-1	
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$	N-CH			± 100	nA
		$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$	P-CH			± 100	
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	N-CH	1		2.5	V
		$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	P-CH	-1		-2.5	
Static Drain-Source On-Resistance (Note 2)	$R_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=6.5\text{A}$	N-CH		15	25	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=5\text{A}$			20	30	
		$V_{GS}=-10\text{V}, I_D=-4.5\text{A}$	P-CH		24	33	
		$V_{GS}=-4.5\text{V}, I_D=-4.2\text{A}$			35	44	
Diode Forward Voltage	V_{SD}	$I_S=1.7\text{A}, V_{GS}=0\text{V}$	N-CH			1.2	V
		$I_S=-1.7\text{A}, V_{GS}=0\text{V}$	P-CH			-1.2	
Dynamic							
Input Capacitance	C_{iss}	N-Channel: $V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$ P-Channel: $V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1\text{MHz}$	N-CH		460		pF
Output Capacitance	C_{oss}		P-CH		840		
Reverse Transfer Capacitance	C_{rss}		N-CH		70		
Total Gate Charge	Q_g		P-CH		120		
Gate Source Charge	Q_{gs}		N-CH		17		
Gate Drain Charge	Q_{gd}		P-CH		32		
Turn-On Delay Time	$t_{d(on)}$	N-Channel: $V_{DD}=15\text{V}, R_L=15\Omega, I_D=1\text{A}, V_{GEN}=10\text{V}, R_G=6\Omega$ P-Channel: $V_{DD}=-15\text{V}, R_L=15\Omega, I_D=-1\text{A}, V_{GEN}=-10\text{V}, R_G=6\Omega$	N-CH		9.3		ns
Turn-On Rise Time	t_r		P-CH		32		
Turn-Off Delay Time	$t_{d(off)}$		N-CH		14		
Turn-Off Fall Time	t_f		P-CH		13		
			N-CH		32		
			P-CH		28		
			N-CH		3.2		
			P-CH		6.8		

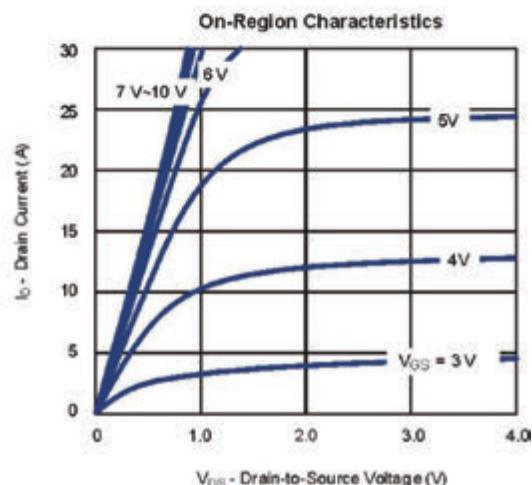
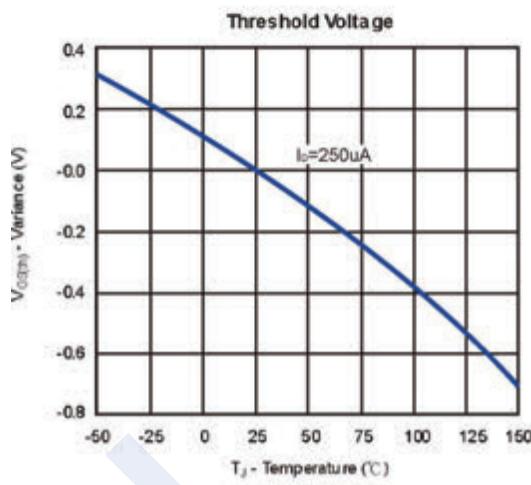
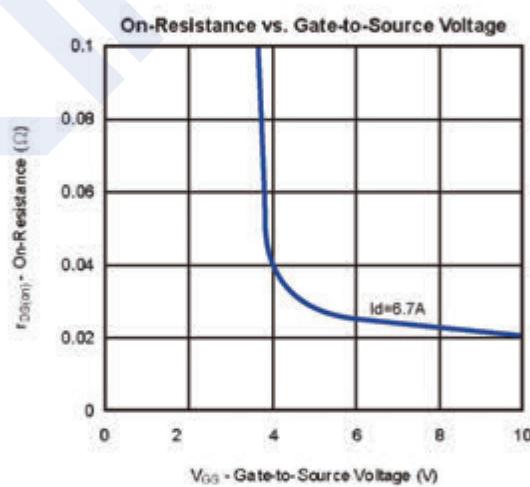
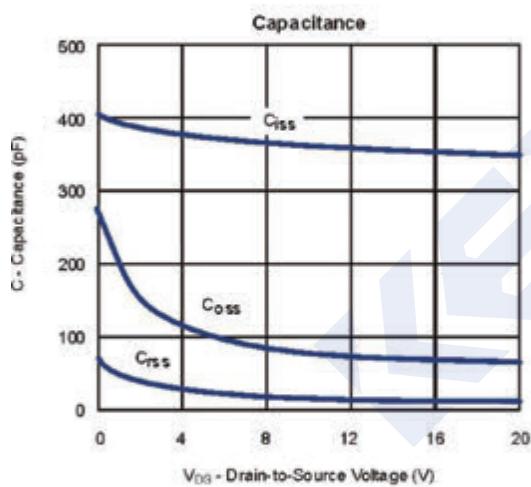
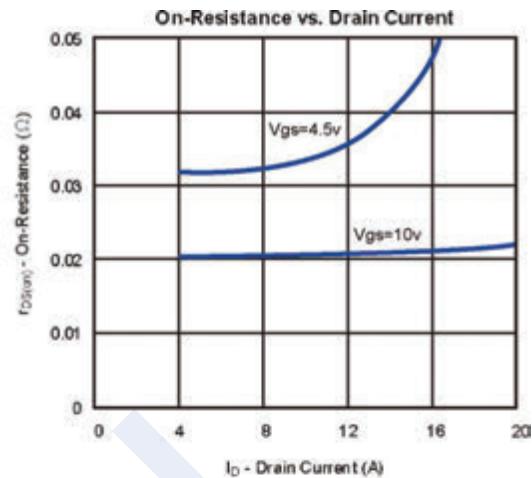
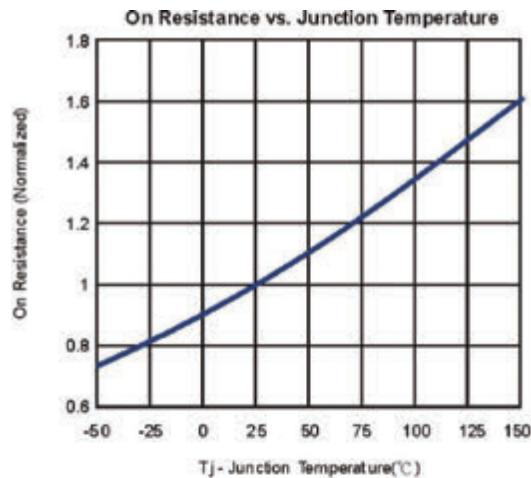
Note 2. Pulse Test: Pulse Width $\leqslant 300\mu\text{s}$, Duty Cycle $\leqslant 2\%$.

■ Marking

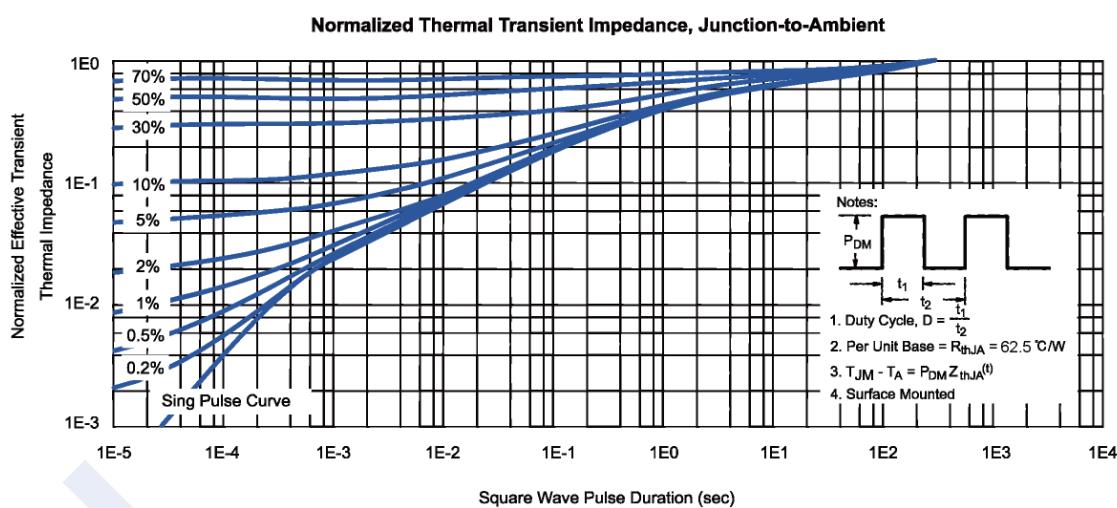
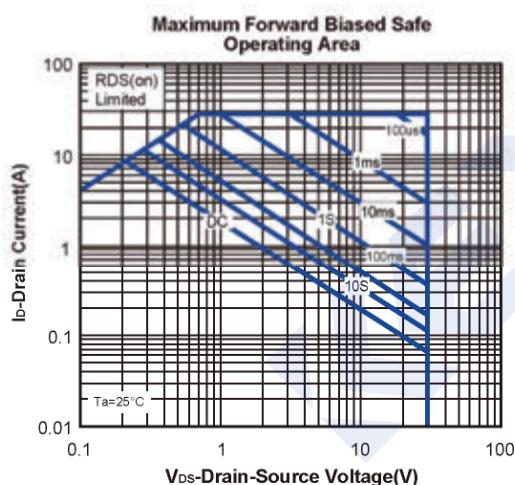
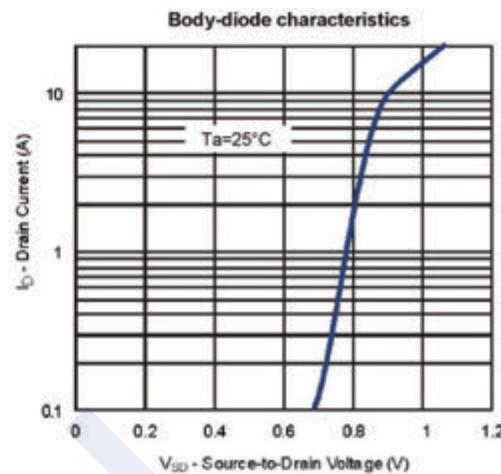
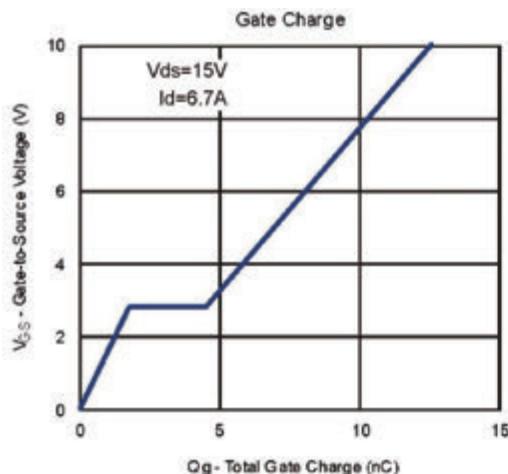
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■ N-Channel Typical Electrical and Thermal Characteristics Curves

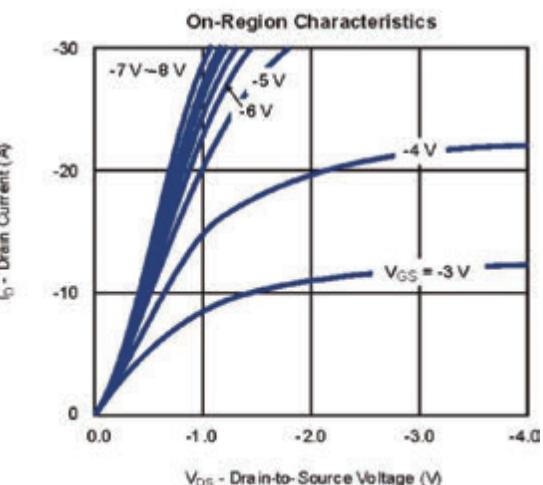
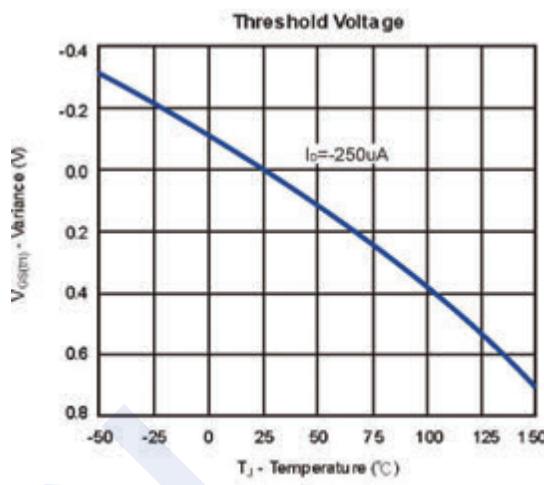
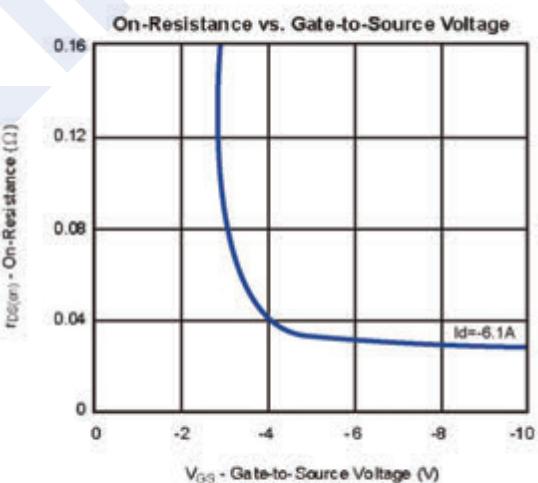
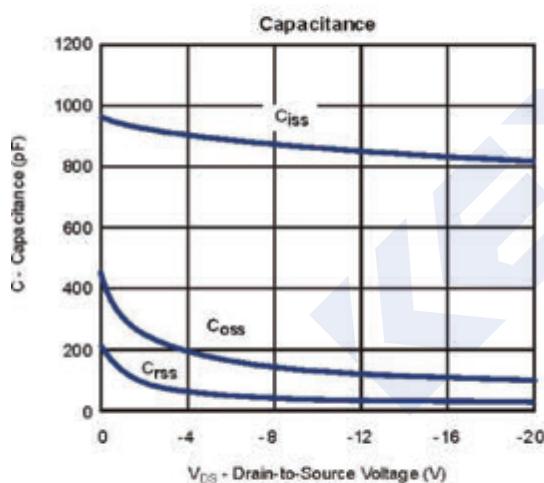
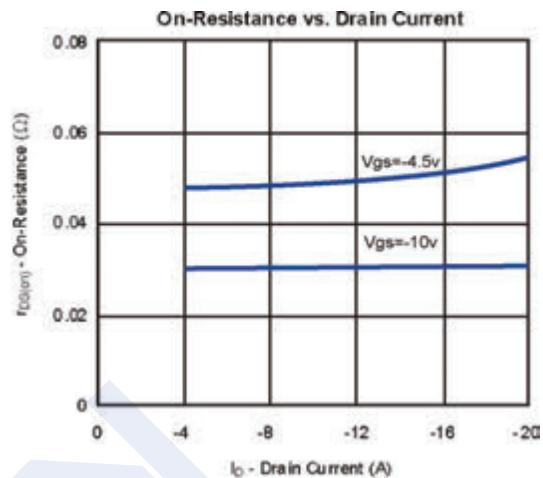
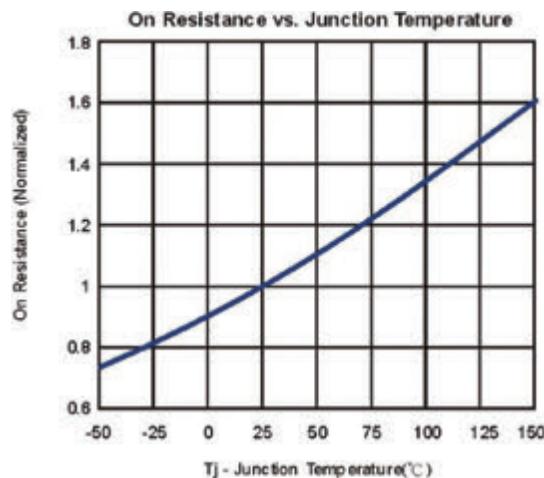


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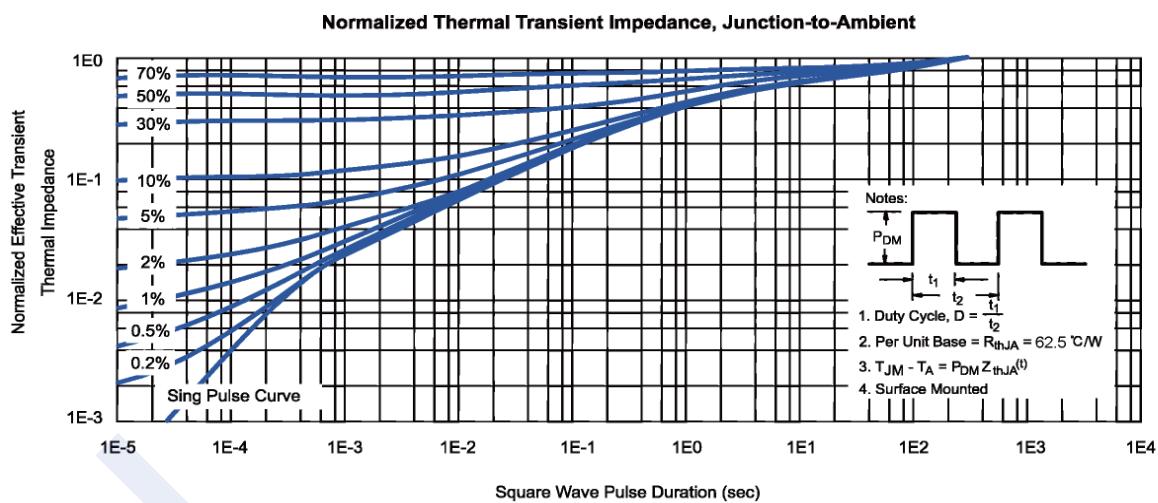
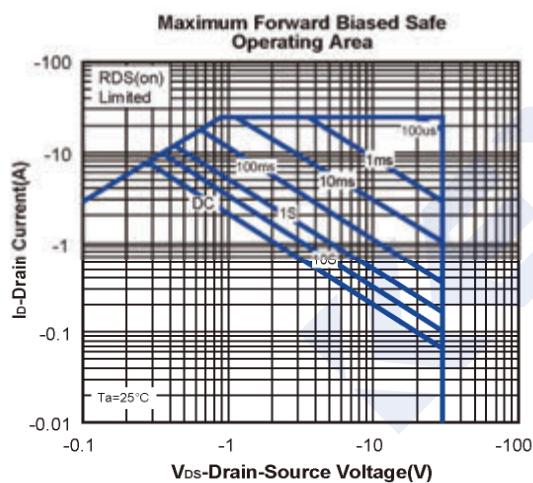
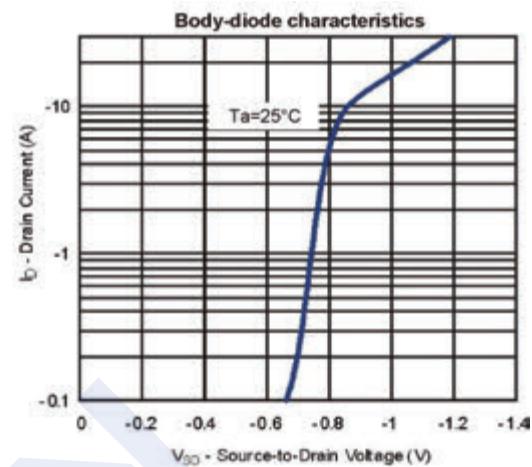
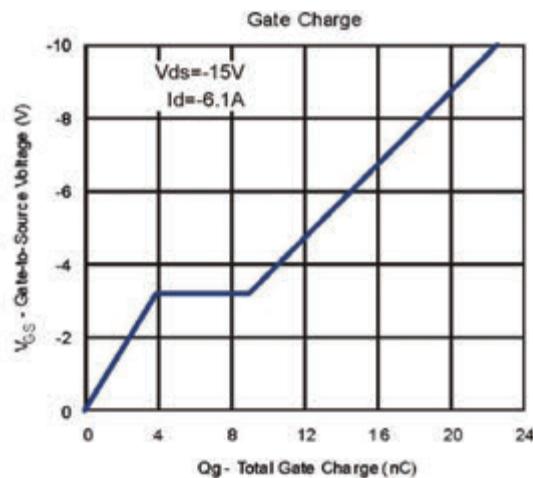


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■ P-Channel Typical Electrical and Thermal Characteristics Curves

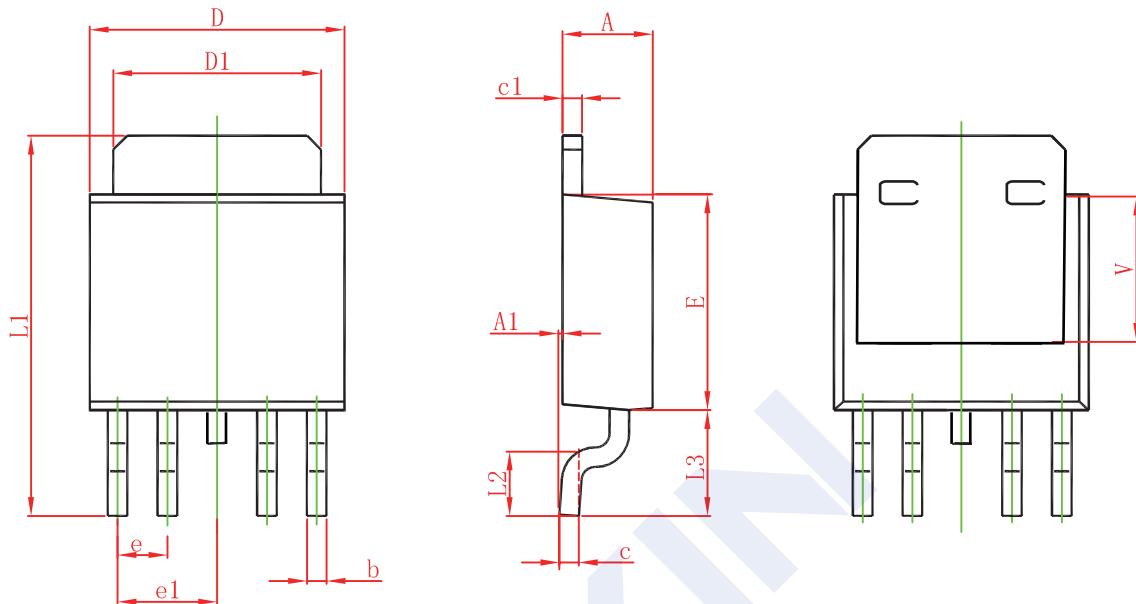


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■ TO-252-4L Package Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.400	0.600	0.016	0.024
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	1.270 TYP		0.050 TYP	
e1	2.540 TYP		1.000 TYP	
L1	9.500	9.900	0.374	0.390
L2	1.400	1.780	0.055	0.070
L3	2.550	2.900	0.100	0.114
V	3.45 REF		0.136 REF	